

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

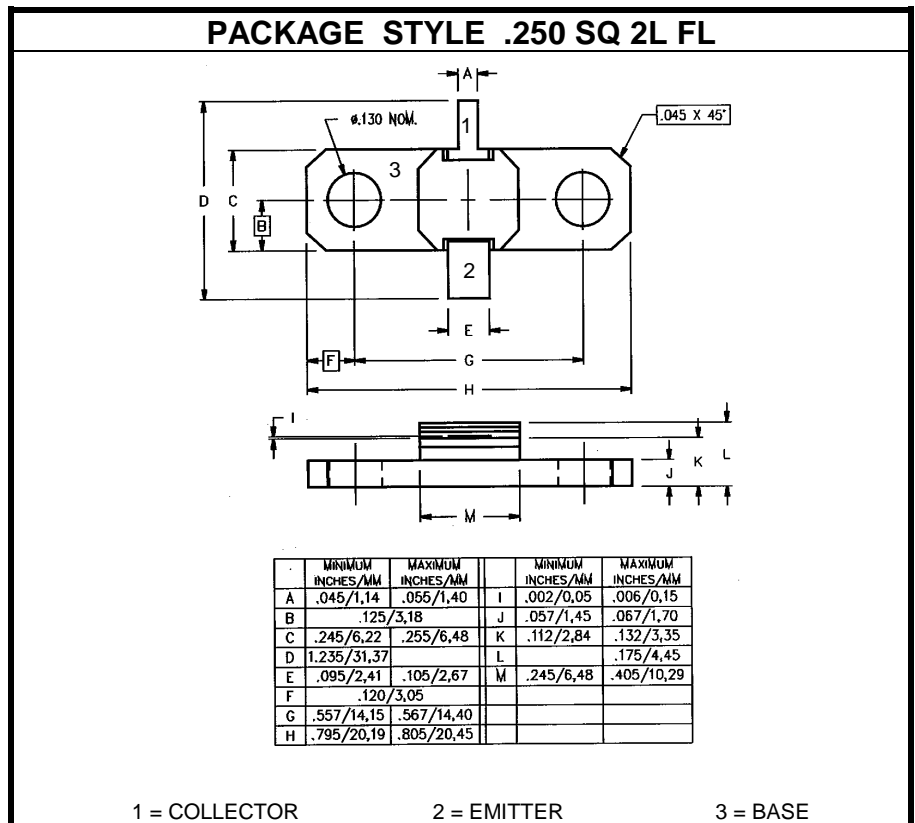
The **ASI SD1528-08** is Common Base Device Designed for IFF, DME and TACAN Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Emitter Ballasting

MAXIMUM RATINGS

I_C	1.5 A
V_{CEO}	65 V
V_{EBO}	3.5 V
P_{DISS}	87 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	2.0 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			
BV_{CES}	$I_C = 25$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CES}	$V_{CE} = 50$ V			2.0	mA
P_G	$V_{CE} = 50$ V $P_{IN} = 1.5$ W PULSE WIDTH = 10 μ S	10			dB
P_{OUT}		15			W
η		30			%